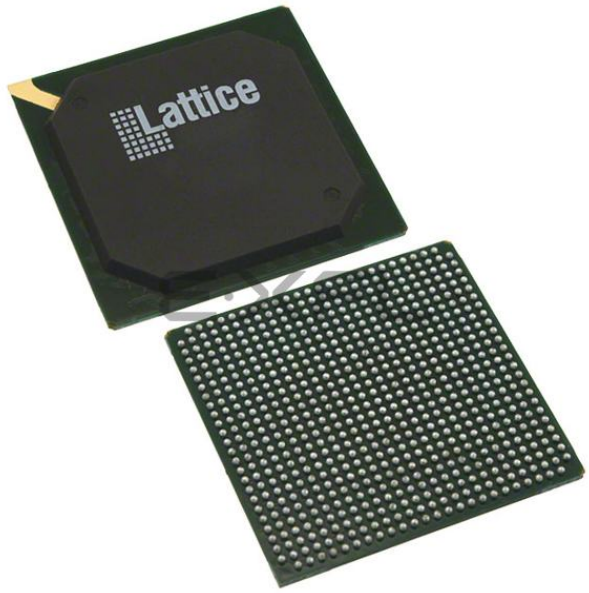
Lattice Semiconductor Corporation - LFE3-95E-6FN672C Datasheet



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The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	11500
Number of Logic Elements/Cells	92000
Total RAM Bits	4526080
Number of I/O	380
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-95e-6fn672c

Introduction

The LatticeECP3™ (EConomy Plus Third generation) family of FPGA devices is optimized to deliver high performance features such as an enhanced DSP architecture, high speed SERDES and high speed source synchronous interfaces in an economical FPGA fabric. This combination is achieved through advances in device architecture and the use of 65nm technology making the devices suitable for high-volume, high-speed, low-cost applications.

The LatticeECP3 device family expands look-up-table (LUT) capacity to 149K logic elements and supports up to 486 user I/Os. The LatticeECP3 device family also offers up to 320 18x18 multipliers and a wide range of parallel I/O standards.

The LatticeECP3 FPGA fabric is optimized with high performance and low cost in mind. The LatticeECP3 devices utilize reconfigurable SRAM logic technology and provide popular building blocks such as LUT-based logic, distributed and embedded memory, Phase Locked Loops (PLLs), Delay Locked Loops (DLLs), pre-engineered source synchronous I/O support, enhanced sysDSP slices and advanced configuration support, including encryption and dual-boot capabilities.

The pre-engineered source synchronous logic implemented in the LatticeECP3 device family supports a broad range of interface standards, including DDR3, XGMII and 7:1 LVDS.

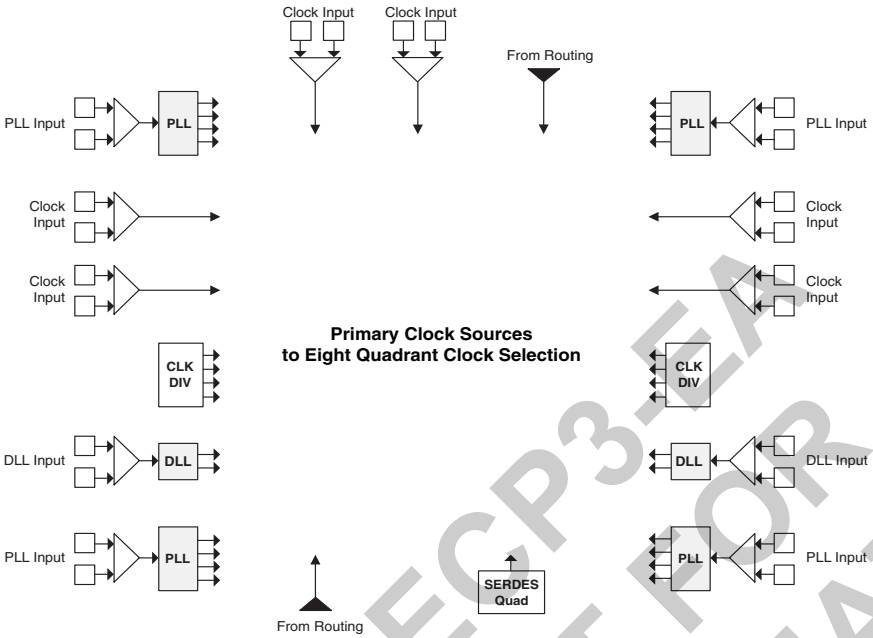
The LatticeECP3 device family also features high speed SERDES with dedicated PCS functions. High jitter tolerance and low transmit jitter allow the SERDES plus PCS blocks to be configured to support an array of popular data protocols including PCI Express, SMPTE, Ethernet (XAUI, GbE, and SGMII) and CPRI. Transmit Pre-emphasis and Receive Equalization settings make the SERDES suitable for transmission and reception over various forms of media.

The LatticeECP3 devices also provide flexible, reliable and secure configuration options, such as dual-boot capability, bit-stream encryption, and TransFR field upgrade features.

The ispLEVER® design tool suite from Lattice allows large complex designs to be efficiently implemented using the LatticeECP3 FPGA family. Synthesis library support for LatticeECP3 is available for popular logic synthesis tools. The ispLEVER tool uses the synthesis tool output along with the constraints from its floor planning tools to place and route the design in the LatticeECP3 device. The ispLEVER tool extracts the timing from the routing and back-annotates it into the design for timing verification.

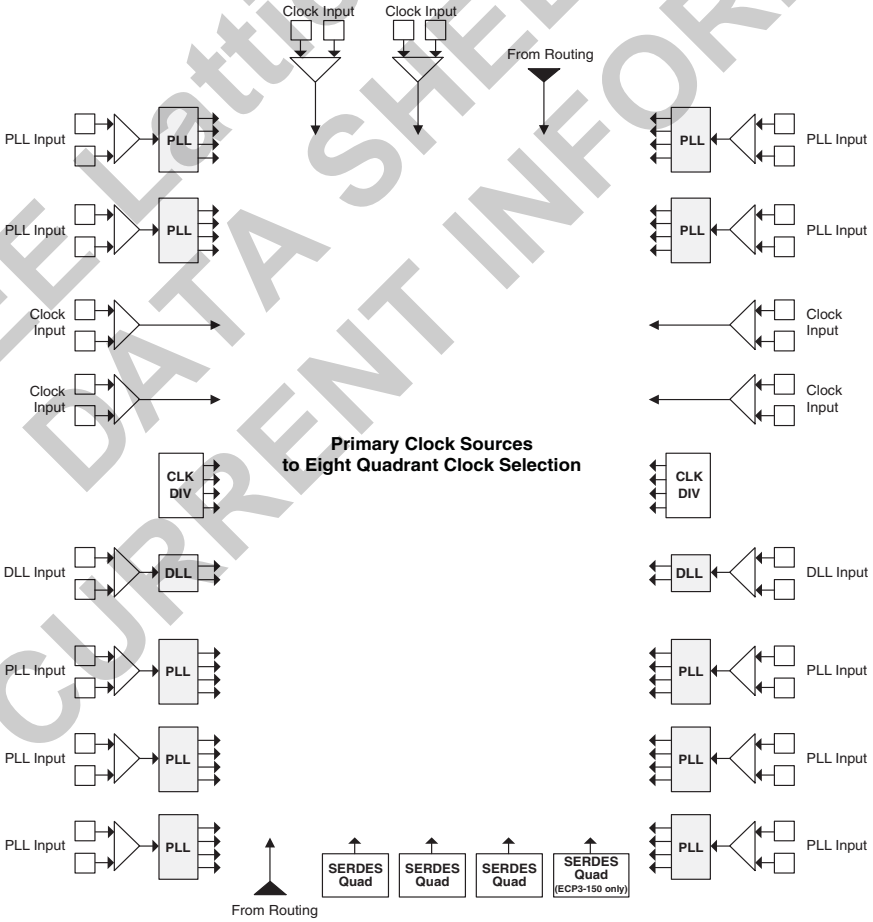
Lattice provides many pre-engineered IP (Intellectual Property) ispLeverCORE™ modules for the LatticeECP3 family. By using these configurable soft core IPs as standardized blocks, designers are free to concentrate on the unique aspects of their design, increasing their productivity.

Figure 2-10. Primary Clock Sources for LatticeECP3-35



Note: Clock inputs can be configured in differential or single-ended mode.

Figure 2-11. Primary Clock Sources for LatticeECP3-70, -95, -150



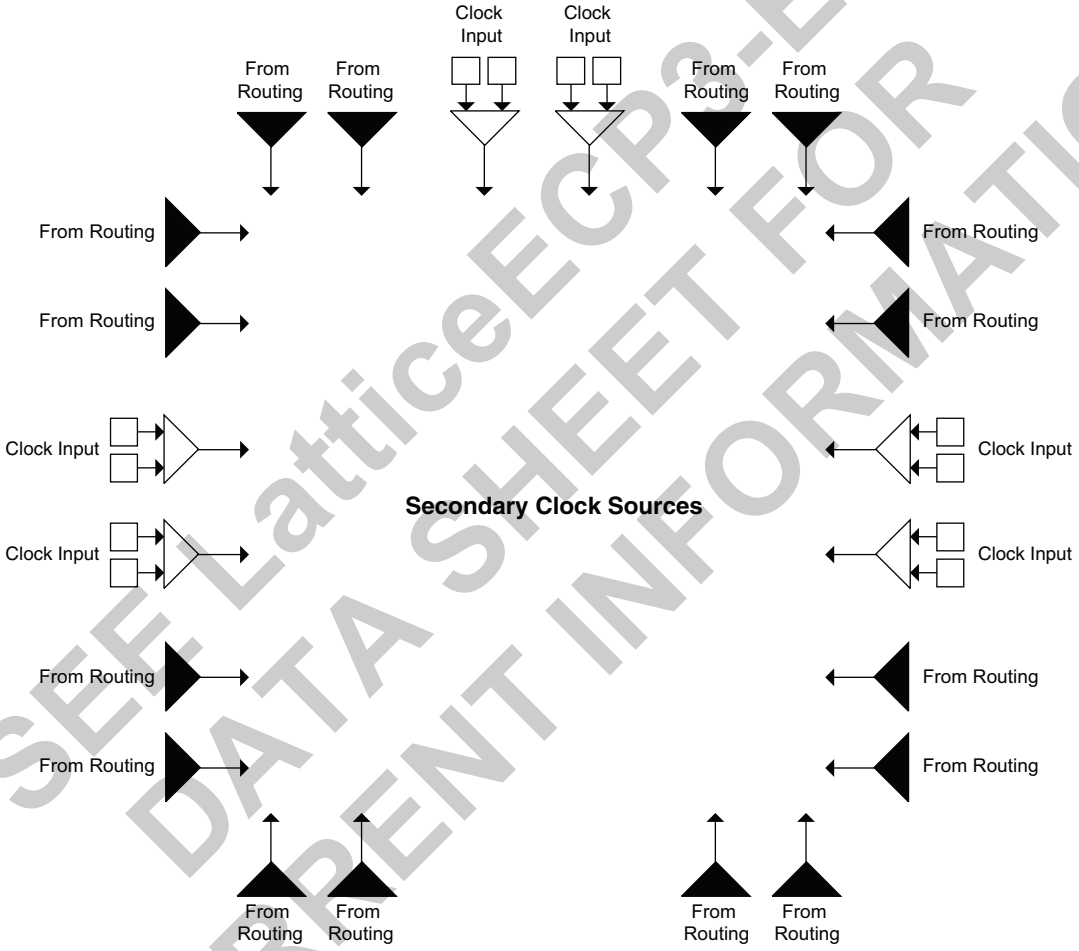
Note: Clock inputs can be configured in differential or single-ended mode.

Secondary Clock/Control Sources

LatticeECP3 devices derive eight secondary clock sources (SC0 through SC7) from six dedicated clock input pads and the rest from routing. Figure 2-14 shows the secondary clock sources. All eight secondary clock sources are defined as inputs to a per-region mux SC0-SC7. SC0-SC3 are primary for control signals (CE and/or LSR), and SC4-SC7 are for clock and high fanout data.

In an actual implementation, there is some overlap to maximize routability. In addition to SC0-SC3, SC7 is also an input to the control signals (LSR or CE). SC0-SC2 are also inputs to clocks along with SC4-SC7. High fanout logic signals (LUT inputs) will utilize the X2 and X0 switches where SC0-SC7 are inputs to X2 switches, and SC4-SC7 are inputs to X0 switches. Note that through X0 switches, SC4-SC7 can also access control signals CE/LSR.

Figure 2-14. Secondary Clock Sources



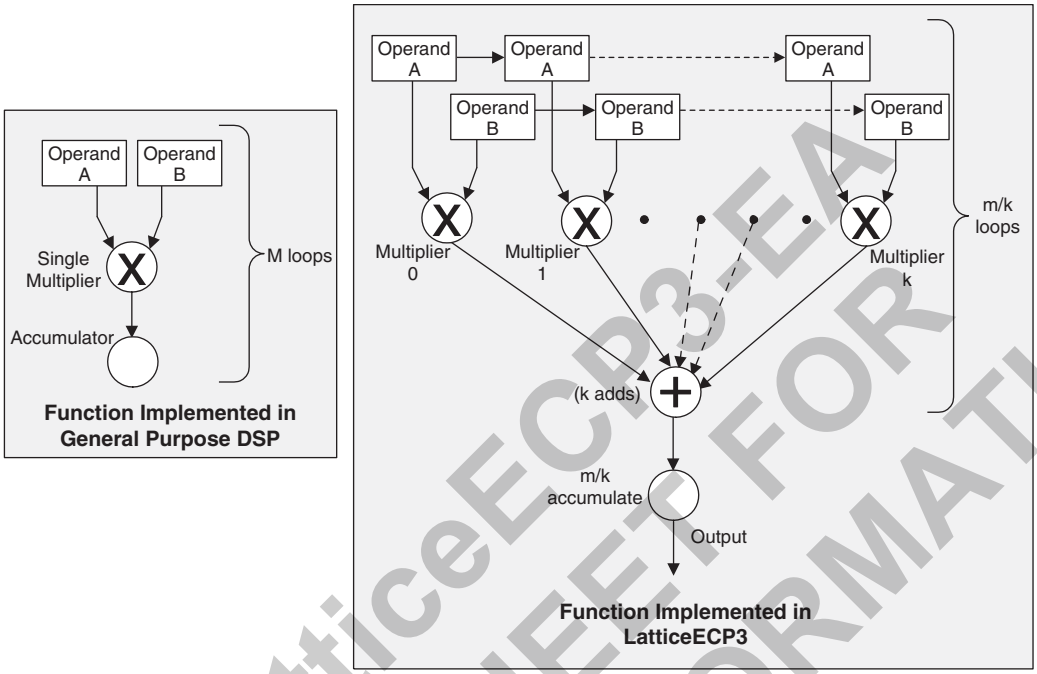
Note: Clock inputs can be configured in differential or single-ended mode.

Secondary Clock/Control Routing

Global secondary clock is a secondary clock that is distributed to all regions. The purpose of the secondary clock routing is to distribute the secondary clock sources to the secondary clock regions. Secondary clocks in the LatticeECP3 devices are region-based resources. Certain EBR rows and special vertical routing channels bind the secondary clock regions. This special vertical routing channel aligns with either the left edge of the center DSP slice in the DSP row or the center of the DSP row. Figure 2-15 shows this special vertical routing channel and the 20 secondary clock regions for the LatticeECP3 family of devices. All devices in the LatticeECP3 family have eight

This allows designers to use highly parallel implementations of DSP functions. Designers can optimize DSP performance vs. area by choosing appropriate levels of parallelism. Figure 2-23 compares the fully serial implementation to the mixed parallel and serial implementation.

Figure 2-23. Comparison of General DSP and LatticeECP3 Approaches



LatticeECP3 sysDSP Slice Architecture Features

The LatticeECP3 sysDSP Slice has been significantly enhanced to provide functions needed for advanced processing applications. These enhancements provide improved flexibility and resource utilization.

The LatticeECP3 sysDSP Slice supports many functions that include the following:

- Multiply (one 18x36, two 18x18 or four 9x9 Multiplies per Slice)
- Multiply (36x36 by cascading across two sysDSP slices)
- Multiply Accumulate (up to 18x36 Multipliers feeding an Accumulator that can have up to 54-bit resolution)
- Two Multiplies feeding one Accumulate per cycle for increased processing with lower latency (two 18x18 Multiplies feed into an accumulator that can accumulate up to 52 bits)
- Flexible saturation and rounding options to satisfy a diverse set of applications situations
- Flexible cascading across DSP slices
  - Minimizes fabric use for common DSP and ALU functions
  - Enables implementation of FIR Filter or similar structures using dedicated sysDSP slice resources only
  - Provides matching pipeline registers
  - Can be configured to continue cascading from one row of sysDSP slices to another for longer cascade chains
- Flexible and Powerful Arithmetic Logic Unit (ALU) Supports:
  - Dynamically selectable ALU OPCODE
  - Ternary arithmetic (addition/subtraction of three inputs)
  - Bit-wise two-input logic operations (AND, OR, NAND, NOR, XOR and XNOR)
  - Eight flexible and programmable ALU flags that can be used for multiple pattern detection scenarios, such

2. **Left and Right (Banks 2, 3, 6 and 7) sysI/O Buffer Pairs (50% Differential and 100% Single-Ended Outputs)**
   The sysI/O buffer pairs in the left and right banks of the device consist of two single-ended output drivers, two sets of single-ended input buffers (both ratioed and referenced) and one differential output driver. One of the referenced input buffers can also be configured as a differential input. In these banks the two pads in the pair are described as “true” and “comp”, where the true pad is associated with the positive side of the differential I/O, and the comp (complementary) pad is associated with the negative side of the differential I/O.

   In addition, programmable on-chip input termination (parallel or differential, static or dynamic) is supported on these sides, which is required for DDR3 interface. However, there is no support for hot-socketing on these sides as the clamp is always present.

   LVDS, RSDS, PPLVDS and Mini-LVDS differential output drivers are available on 50% of the buffer pairs on the left and right banks.

3. **Configuration Bank sysI/O Buffer Pairs (Single-Ended Outputs, Only on Shared Pins When Not Used by Configuration)**
   The sysI/O buffers in the Configuration Bank consist of single-ended output drivers and single-ended input buffers (both ratioed and referenced). The referenced input buffer can also be configured as a differential input.

   The two pads in the pair are described as “true” and “comp”, where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

Programmable PCI clamps are only available on top banks (PCI clamps are used primarily on inputs and bidirectional pads to reduce ringing on the receiving end) can also be used on inputs.

Typical sysI/O I/O Behavior During Power-up

The internal power-on-reset (POR) signal is deactivated when V_{CC}, V_{CCIO8} and V_{CCAUX} have reached satisfactory levels. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user’s responsibility to ensure that all other V_{CCIO} banks are active with valid input logic levels to properly control the output logic states of all the I/O banks that are critical to the application. For more information about controlling the output logic state with valid input logic levels during power-up in LatticeECP3 devices, see the list of technical documentation at the end of this data sheet.

The V_{CC} and V_{CCAUX} supply the power to the FPGA core fabric, whereas the V_{CCIO} supplies power to the I/O buffers. In order to simplify system design while providing consistent and predictable I/O behavior, it is recommended that the I/O buffers be powered-up prior to the FPGA core fabric. V_{CCIO} supplies should be powered-up before or together with the V_{CC} and V_{CCAUX} supplies.

Supported sysI/O Standards

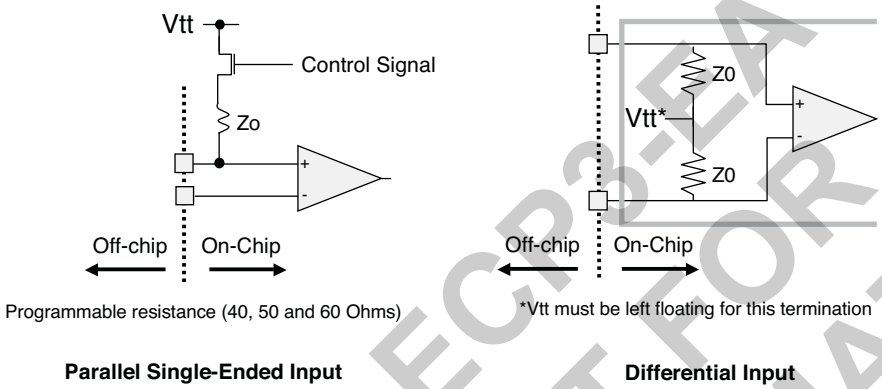
The LatticeECP3 sysI/O buffer supports both single-ended and differential standards. Single-ended standards can be further subdivided into LVCMOS, LVTTL and other standards. The buffers support the LVTTL, LVCMOS 1.2V, 1.5V, 1.8V, 2.5V and 3.3V standards. In the LVCMOS and LVTTL modes, the buffer has individual configuration options for drive strength, slew rates, bus maintenance (weak pull-up, weak pull-down, or a bus-keeper latch) and open drain. Other single-ended standards supported include SSTL and HSTL. Differential standards supported include LVDS, BLVDS, LVPECL, MLVDS, RSDS, Mini-LVDS, PPLVDS (point-to-point LVDS), TRLVDS (Transition Reduced LVDS), differential SSTL and differential HSTL. Tables 2-13 and 2-14 show the I/O standards (together with their supply and reference voltages) supported by LatticeECP3 devices. For further information on utilizing the sysI/O buffer to support a variety of standards please see TN1177, LatticeECP3 sysIO Usage Guide.

On-Chip Programmable Termination

The LatticeECP3 supports a variety of programmable on-chip terminations options, including:

- Dynamically switchable Single Ended Termination for SSTL15 inputs with programmable resistor values of 40, 50, or 60 ohms. This is particularly useful for low power JEDEC compliant DDR3 memory controller implementations. External termination to Vtt should be used for DDR2 memory controller implementation.
- Common mode termination of 80, 100, 120 ohms for differential inputs

Figure 2-39. On-Chip Termination



See Table 2-12 for termination options for input modes.

Table 2-12. On-Chip Termination Options for Input Modes

IO_TYPE	TERMINATE to VTT[1, 2]	DIFFRENTIAL TERMINATION RESISTOR[1]
LVDS25	þ	80, 100, 120
BLVDS25	þ	80, 100, 120
MLVDS	þ	80, 100, 120
HSTL18_I	40, 50, 60	þ
HSTL18_II	40, 50, 60	þ
HSTL18D_I	40, 50, 60	þ
HSTL18D_II	40, 50, 60	þ
HSTL15_I	40, 50, 60	þ
HSTL15D_I	40, 50, 60	þ
SSTL25_I	40, 50, 60	þ
SSTL25_II	40, 50, 60	þ
SSTL25D_I	40, 50, 60	þ
SSTL25D_II	40, 50, 60	þ
SSTL18_I	40, 50, 60	þ
SSTL18_II	40, 50, 60	þ
SSTL18D_I	40, 50, 60	þ
SSTL18D_II	40, 50, 60	þ
SSTL15	40, 50, 60	þ
SSTL15D	40, 50, 60	þ

1. TERMINATE to VTT and DIFFRENTIAL TERMINATION RESISTOR when turn on can only have one setting per bank. Only left and right banks have this feature.
   Use of TERMINATE to VTT and DIFFRENTIAL TERMINATION RESISTOR are mutually exclusive in an I/O bank.
   On-chip termination tolerance +/- 20%
2. External termination to VTT should be used when implementing DDR2 memory controller.

Please see TN1177, LatticeECP3 sysIO Usage Guide for on-chip termination usage and value ranges.

Equalization Filter

Equalization filtering is available for single-ended inputs on both true and complementary I/Os, and for differential inputs on the true I/Os on the left, right, and top sides. Equalization is required to compensate for the difficulty of sampling alternating logic transitions with a relatively slow slew rate. It is considered the most useful for the Input DDRX2 modes, used in DDR3 memory, LVDS, or TRLVDS signaling. Equalization filter acts as a tunable filter with settings to determine the level of correction. In the LatticeECP3 devices, there are four settings available: 0 (none), 1, 2 and 3. The default setting is 0. The equalization logic resides in the sysI/O buffers, the two bits of setting is set uniquely in each input IOLOGIC block. Therefore, each sysI/O can have a unique equalization setting within a DQS-12 group.

Hot Socketing

LatticeECP3 devices have been carefully designed to ensure predictable behavior during power-up and power-down. During power-up and power-down sequences, the I/Os remain in tri-state until the power supply voltage is high enough to ensure reliable operation. In addition, leakage into I/O pins is controlled within specified limits. Please refer to the Hot Socketing Specifications in the DC and Switching Characteristics in this data sheet.

SERDES and PCS (Physical Coding Sublayer)

LatticeECP3 devices feature up to 16 channels of embedded SERDES/PCS arranged in quads at the bottom of the devices supporting up to 3.2Gbps data rate. Figure 2-40 shows the position of the quad blocks for the LatticeECP3-150 devices. Table 2-14 shows the location of available SERDES Quads for all devices.

The LatticeECP3 SERDES/PCS supports a range of popular serial protocols, including:

- PCI Express 1.1
- Ethernet (XAUI, GbE - 1000 Base CS/SX/LX and SGMII)
- Serial RapidIO
- SMPTE SDI (3G, HD, SD)
- CPRI
- SONET/SDH (STS-3, STS-12, STS-48)

Each quad contains four dedicated SERDES for high speed, full duplex serial data transfer. Each quad also has a PCS block that interfaces to the SERDES channels and contains protocol specific digital logic to support the standards listed above. The PCS block also contains interface logic to the FPGA fabric. All PCS logic for dedicated protocol support can also be bypassed to allow raw 8-bit or 10-bit interfaces to the FPGA fabric.

Even though the SERDES/PCS blocks are arranged in quads, multiple baud rates can be supported within a quad with the use of dedicated, per channel ÷1, ÷2 and ÷11 rate dividers. Additionally, multiple quads can be arranged together to form larger data pipes.

For information on how to use the SERDES/PCS blocks to support specific protocols, as well on how to combine multiple protocols and baud rates within a device, please refer to TN1176, LatticeECP3 SERDES/PCS Usage Guide.

LatticeECP3 Family Data Sheet DC and Switching Characteristics

Absolute Maximum Ratings[1, 2, 3]

Supply Voltage V_{CC} . . . . . -0.5 to 1.32V

Supply Voltage V_{CCAUX} . . . . . -0.5 to 3.75V

Supply Voltage V_{CCJ} . . . . . -0.5 to 3.75V

Output Supply Voltage V_{CCIO} . . . . . -0.5 to 3.75V

Input or I/O Tristate Voltage Applied[4]. . . . . -0.5 to 3.75V

Storage Temperature (Ambient) . . . . . -65 to 150°C

Junction Temperature (Tj) . . . . . +125°C

1. Stress above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.
2. Compliance with the Lattice Thermal Management document is required.
3. All voltages referenced to GND.
4. Overshoot and undershoot of -2V to (V_{IHMAX} + 2) volts is permitted for a duration of <20ns.

Recommended Operating Conditions[1]

Symbol	Parameter	Min.	Max.	Units
V_{CC}[2]	Core Supply Voltage	1.14	1.26	V
V_{CCAUX}[2, 4]	Auxiliary Supply Voltage, Terminating Resistor Switching Power Supply (SERDES)	3.135	3.465	V
V_{CCPLL}	PLL Supply Voltage	3.135	3.465	V
V_{CCIO}[2, 3]	I/O Driver Supply Voltage	1.14	3.465	V
V_{CCJ}[2]	Supply Voltage for IEEE 1149.1 Test Access Port	1.14	3.465	V
V_{REF1} and V_{REF2}	Input Reference Voltage	0.5	1.7	V
V_{TT}[5]	Termination Voltage	0.5	1.3125	V
t_{JCOM}	Junction Temperature, Commercial Operation	0	85	°C
t_{JIND}	Junction Temperature, Industrial Operation	-40	100	°C
SERDES External Power Supply[6]				
V_{CCIB}	Input Buffer Power Supply (1.2V)	1.14	1.26	V
	Input Buffer Power Supply (1.5V)	1.425	1.575	V
V_{CCOB}	Output Buffer Power Supply (1.2V)	1.14	1.26	V
	Output Buffer Power Supply (1.5V)	1.425	1.575	V
V_{CCA}	Transmit, Receive, PLL and Reference Clock Buffer Power Supply	1.14	1.26	V

1. For correct operation, all supplies except V_{REF} and V_{TT} must be held in their valid operation range. This is true independent of feature usage.
2. If V_{CCIO} or V_{CCJ} is set to 1.2V, they must be connected to the same power supply as V_{CC}. If V_{CCIO} or V_{CCJ} is set to 3.3V, they must be connected to the same power supply as V_{CCAUX}.
3. See recommended voltages by I/O standard in subsequent table.
4. V_{CCAUX} ramp rate must not exceed 30mV/µs during power-up when transitioning between 0V and 3.3V.
5. If not used, V_{TT} should be left floating.
6. See TN1176, LatticeECP3 SERDES/PCS Usage Guide for information on board considerations for SERDES power supplies.

sysI/O Recommended Operating Conditions

Standard	V_{CCIO}			V_{REF} (V)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
LVCMOS33[2]	3.135	3.3	3.465	—	—	—
LVCMOS25[2]	2.375	2.5	2.625	—	—	—
LVCMOS18	1.71	1.8	1.89	—	—	—
LVCMOS15	1.425	1.5	1.575	—	—	—
LVCMOS12[2]	1.14	1.2	1.26	—	—	—
LVTTL33[2]	3.135	3.3	3.465	—	—	—
PCI33	3.135	3.3	3.465	—	—	—
SSTL15[3]	1.43	1.5	1.57	0.68	0.75	0.9
SSTL18_I, II[2]	1.71	1.8	1.89	0.833	0.9	0.969
SSTL25_I, II[2]	2.375	2.5	2.625	1.15	1.25	1.35
SSTL33_I, II[2]	3.135	3.3	3.465	1.3	1.5	1.7
HSTL15_I[2]	1.425	1.5	1.575	0.68	0.75	0.9
HSTL18_I, II[2]	1.71	1.8	1.89	0.816	0.9	1.08
LVDS25[2]	2.375	2.5	2.625	—	—	—
MLVDS25[1]	2.375	2.5	2.625	—	—	—
LVPECL33[1, 2]	3.135	3.3	3.465	—	—	—
Mini LVDS	—	—	—	—	—	—
BLVDS25[1, 2]	2.375	2.5	2.625	—	—	—
RSDS25[1, 2]	2.375	2.5	2.625	—	—	—
RSDS25E[1, 2]	2.375	2.5	2.625	—	—	—
TRLVDS	3.14	3.3	3.47	—	—	—
PPLVDS	3.14/2.25	3.3/2.5	3.47/2.75	—	—	—
SSTL15D	1.43	1.5	1.57	—	—	—
SSTL18D_I[2], II[2]	1.71	1.8	1.89	—	—	—
SSTL25D_ I[2], II[2]	2.375	2.5	2.625	—	—	—
SSTL33D_ I[2], II[2]	3.135	3.3	3.465	—	—	—
HSTL15D_ I[2]	1.425	1.5	1.575	—	—	—
HSTL18D_ I[2], II[2]	1.71	1.8	1.89	—	—	—

1. Inputs on chip. Outputs are implemented with the addition of external resistors.
2. For input voltage compatibility, refer to the "Mixed Voltage Support" section of TN1177, LatticeECP3 sysIO Usage Guide.

RSDS25E

The LatticeECP3 devices support differential RSDS and RSDSE standards. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The RSDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-4 is one possible solution for RSDS standard implementation. Resistor values in Figure 3-4 are industry standard values for 1% resistors.

Figure 3-4. RSDS25E (Reduced Swing Differential Signaling)

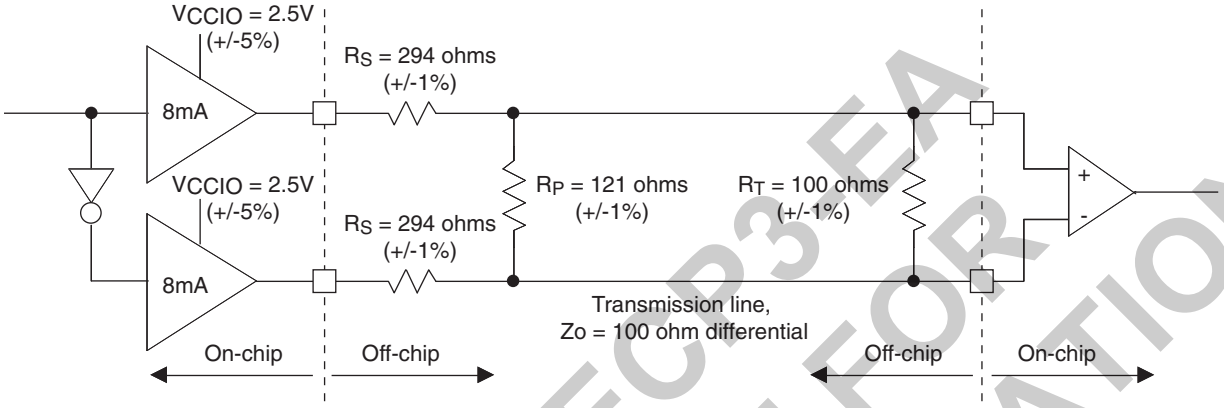


Table 3-4. RSDS25E DC Conditions[1]

Over Recommended Operating Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply (+/-5%)	2.50	V
Z_{OUT}	Driver Impedance	20	Ω
R_S	Driver Series Resistor (+/-1%)	294	Ω
R_P	Driver Parallel Resistor (+/-1%)	121	Ω
R_T	Receiver Termination (+/-1%)	100	Ω
V_{OH}	Output High Voltage	1.35	V
V_{OL}	Output Low Voltage	1.15	V
V_{OD}	Output Differential Voltage	0.20	V
V_{CM}	Output Common Mode Voltage	1.25	V
Z_{BACK}	Back Impedance	101.5	Ω
I_{DC}	DC Output Current	3.66	mA

1. For input buffer, see LVDS table.

LatticeECP3 External Switching Characteristics (Continued)[1, 2]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	-8		-7		-6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Generic DDRX2 Output with Clock and Data (> 10 Bits Wide) Aligned at Pin (GDDRX2_TX.ECLK.Aligned)									
Left and Right Sides									
$t_{DIBGDDR}$	Data Setup Before CLK	ECP3-150EA	—		—		—		ps
$t_{DIAGDDR}$	Data Hold After CLK	ECP3-150EA	—		—		—		ps
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	—		—		—		MHz
Generic DDRX2 Outputs with Clock and Data Edges Aligned, Without PLL 90-degree shifted clock output[5] (GDDRX2_TX.Aligned)									
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-70E/95E	—	200	—	225	—	250	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-70E/95E	—	200	—	225	—	250	ps
f_{MAX_GDDR}	DDR/DDRX2 Clock Frequency[8]	ECP3-70E/95E	—	500	—	420	—	375	MHz
Generic DDRX2 Output with Clock and Data (> 10 Bits Wide) Centered at Pin Using DQSDLL (GDDRX2_TX.DQS-DLL.Centered)									
Left and Right Sides									
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-150EA		—		—		—	ns
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-150EA		—		—		—	ns
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	—		—		—		ns
Generic DDRX2 Output with Clock and Data (> 10 Bits Wide) Centered at Pin Using PLL (GDDRX2_TX.PLL.Centered)									
Left and Right Sides									
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-150EA		—		—		—	ns
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-150EA		—		—		—	ns
f_{MAX_GDDR}	DDRX2 Clock Frequency	ECP3-150EA	—		—		—		ns
Generic DDRX2 Outputs with Clock Edge in the Center of Data Window, with PLL 90-degree Shifted Clock Output[6] (GDDRX2_TX.PLL.Centered)									
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-70E/95E	300	—	370	—	417	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-70E/95E	300	—	370	—	417	—	ps
f_{MAX_GDDR}	DDR/DDRX2 Clock Frequency[8]	ECP3-70E/95E	—	500	—	420	—	375	MHz

Parameter	Description	Device	-8		-7		-6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
Memory Interface									
DDR/DDR2 SDRAM I/O Pin Parameters (Input Data are Strobe Edge Aligned, Output Strobe Edge is Data Centered)[4]									
t_{DVADQ}	Data Valid After DQS (DDR Read)	ECP3-150EA	—	0.225	—	0.225	—	0.225	UI
t_{DVEDQ}	Data Hold After DQS (DDR Read)	ECP3-150EA	0.64	—	0.64	—	0.64	—	UI
t_{DQVBS}	Data Valid Before DQS	ECP3-150EA	0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Data Valid After DQS	ECP3-150EA	0.25	—	0.25	—	0.25	—	UI
f_{MAX_DDR}	DDR Clock Frequency	ECP3-150EA	95	200	95	200	95	166	MHz
f_{MAX_DDR2}	DDR2 clock frequency	ECP3-150EA	133	266	133	200	133	166	MHz
t_{DVADQ}	Data Valid After DQS (DDR Read)	ECP3-70E/95E	—	0.225	—	0.225	—	0.225	UI
t_{DVEDQ}	Data Hold After DQS (DDR Read)	ECP3-70E/95E	0.64	—	0.64	—	0.64	—	UI
t_{DQVBS}	Data Valid Before DQS	ECP3-70E/95E	0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Data Valid After DQS	ECP3-70E/95E	0.25	—	0.25	—	0.25	—	UI
f_{MAX_DDR}	DDR Clock Frequency	ECP3-70E/95E	95	200	95	200	95	133	MHz

LatticeECP3 Maximum I/O Buffer Speed (Continued)[1, 2, 3, 4, 5, 6]

Over Recommended Operating Conditions

Buffer	Description	Max.	Units
PCI33	PCI, V_{CCIO} = 3.3V	66	MHz

1. These maximum speeds are characterized but not tested on every device.
2. Maximum I/O speed for differential output standards emulated with resistors depends on the layout.
3. LVCMOS timing is measured with the load specified in the Switching Test Conditions table of this document.
4. All speeds are measured at fast slew.
5. Actual system operation may vary depending on user logic implementation.
6. Maximum data rate equals 2 times the clock rate when utilizing DDR.

DLL Timing

Over Recommended Operating Conditions

Parameter	Description	Condition	Min.	Typ.	Max.	Units
f_{REF}	Input reference clock frequency (on-chip or off-chip)		133	—	500	MHz
f_{FB}	Feedback clock frequency (on-chip or off-chip)		133	—	500	MHz
f_{CLKOP}[1]	Output clock frequency, CLKOP		133	—	500	MHz
f_{CLKOS}[2]	Output clock frequency, CLKOS		33.3	—	500	MHz
t_{PJIT}	Output clock period jitter (clean input)			—	200	ps p-p
t_{DUTY}	Output clock duty cycle (at 50% levels, 50% duty cycle input clock, 50% duty cycle circuit turned off, time reference delay mode)	Edge Clock	40		60	%
		Primary Clock	30		70	%
$t_{DUTYTRD}$	Output clock duty cycle (at 50% levels, arbitrary duty cycle input clock, 50% duty cycle circuit enabled, time reference delay mode)	Primary Clock < 250MHz	45		55	%
		Primary Clock ≥ 250MHz	30		70	%
		Edge Clock	45		55	%
$t_{DUTYCIR}$	Output clock duty cycle (at 50% levels, arbitrary duty cycle input clock, 50% duty cycle circuit enabled, clock injection removal mode) with DLL cascading	Primary Clock < 250MHz	40		60	%
		Primary Clock ≥ 250MHz	30		70	%
		Edge Clock	45		55	%
t_{SKEW}[3]	Output clock to clock skew between two outputs with the same phase setting		—	—	100	ps
t_{PHASE}	Phase error measured at device pads between off-chip reference clock and feedback clocks		—	—	+/-400	ps
t_{PWH}	Input clock minimum pulse width high (at 80% level)		550	—	—	ps
t_{PWL}	Input clock minimum pulse width low (at 20% level)		550	—	—	ps
t_{INSTB}	Input clock period jitter		—	—	500	p-p
t_{LOCK}	DLL lock time		8	—	8200	cycles
t_{RSWD}	Digital reset minimum pulse width (at 80% level)		3	—	—	ns
t_{DEL}	Delay step size		27	45	70	ps
t_{RANGE1}	Max. delay setting for single delay block (64 taps)		1.9	3.1	4.4	ns
t_{RANGE4}	Max. delay setting for four chained delay blocks		7.6	12.4	17.6	ns

1. CLKOP runs at the same frequency as the input clock.
2. CLKOS minimum frequency is obtained with divide by 4.
3. This is intended to be a “path-matching” design guideline and is not a measurable specification.

Serial Rapid I/O Type 2 Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-15. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}[1]	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance		80	100	120	Ohms
J_{TX_DDJ}[3, 4, 5]	Output data deterministic jitter		—	—	0.17	UI
J_{TX_TJ}[2, 3, 4, 5]	Total output data jitter		—	—	0.35	UI

1. Rise and Fall times measured with board trace, connector and approximately 2.5pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50-ohm impedance (100-ohm differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
5. Values are measured at 2.5 Gbps.

Table 3-16. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 2.5 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 2.5 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
J_{RX_DJ}[2, 3, 4, 5]	Deterministic jitter tolerance (peak-to-peak)		—	—	0.37	UI
J_{RX_RJ}[2, 3, 4, 5]	Random jitter tolerance (peak-to-peak)		—	—	0.18	UI
J_{RX_SJ}[2, 3, 4, 5]	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.10	UI
J_{RX_TJ}[1, 2, 3, 4, 5]	Total jitter tolerance (peak-to-peak)		—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening		0.35	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-14.
2. Jitter values are measured with each high-speed input AC coupled into a 50-ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 2.5 Gbps.

Gigabit Ethernet/Serial Rapid I/O Type 1/SGMII Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-17. Transmit

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
T_{RF}	Differential rise/fall time	20%-80%	—	80	—	ps
$Z_{TX\_DIFF\_DC}$	Differential impedance		80	100	120	Ohms
J_{TX_DDJ}[3, 4, 5]	Output data deterministic jitter		—	—	0.10	UI
J_{TX_TJ}[2, 3, 4, 5]	Total output data jitter		—	—	0.24	UI

1. Rise and fall times measured with board trace, connector and approximately 2.5pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50-ohm impedance (100-ohm differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
5. Values are measured at 1.25 Gbps.

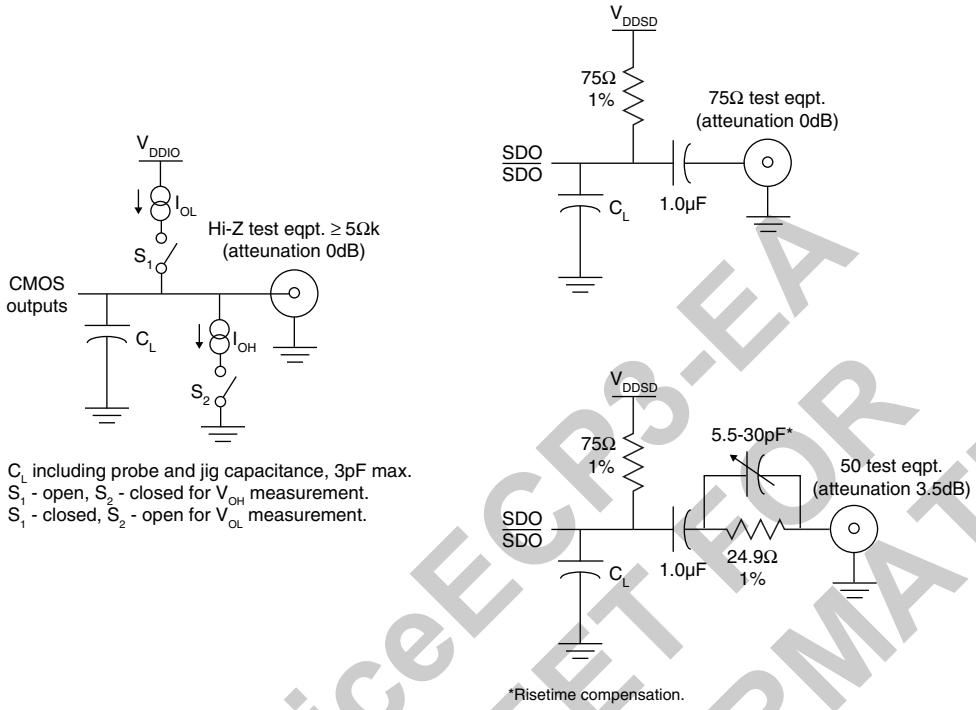
Table 3-18. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min.	Typ.	Max.	Units
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 1.25 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 1.25 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance		80	100	120	Ohms
J_{RX_DJ}[1, 2, 3, 4, 5]	Deterministic jitter tolerance (peak-to-peak)		—	—	0.34	UI
J_{RX_RJ}[1, 2, 3, 4, 5]	Random jitter tolerance (peak-to-peak)		—	—	0.26	UI
J_{RX_SJ}[1, 2, 3, 4, 5]	Sinusoidal jitter tolerance (peak-to-peak)		—	—	0.11	UI
J_{RX_TJ}[1, 2, 3, 4, 5]	Total jitter tolerance (peak-to-peak)		—	—	0.71	UI
T_{RX_EYE}	Receiver eye opening		0.29	—	—	UI

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter. The sinusoidal jitter tolerance mask is shown in Figure 3-14.
2. Jitter values are measured with each high-speed input AC coupled into a 50-ohm impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.
5. Values are measured at 1.25 Gbps.

Figure 3-15. Test Loads

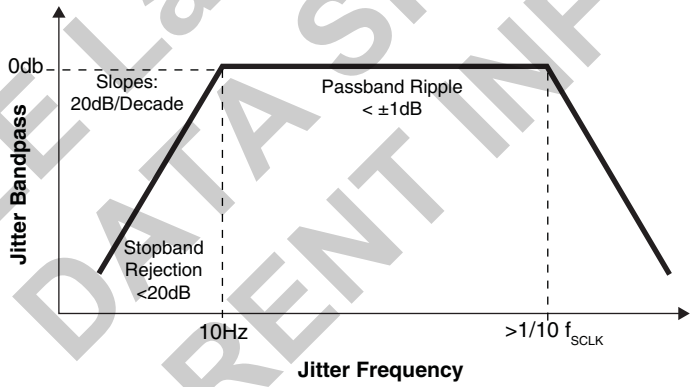
Test Loads



C_L including probe and jig capacitance, 3pF max.
S_1 - open, S_2 - closed for V_{OH} measurement.
S_1 - closed, S_2 - open for V_{OL} measurement.

*Risetime compensation.

Timing Jitter Bandpass



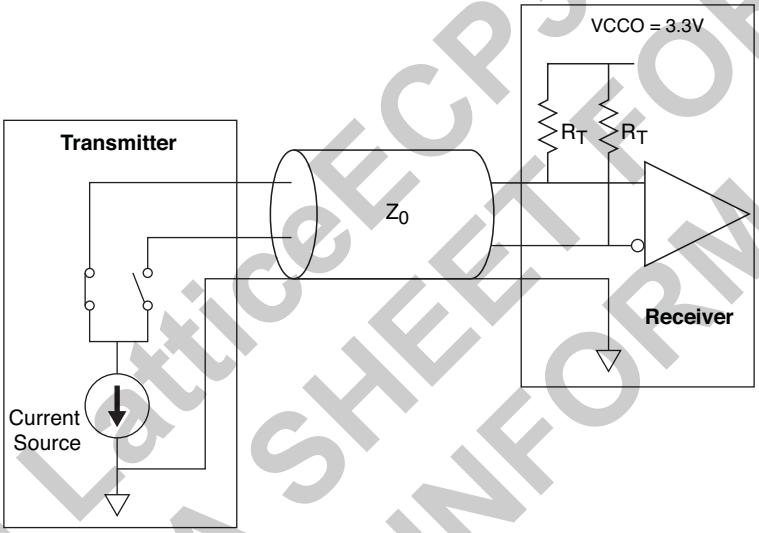
sysI/O Differential Electrical Characteristics

Transition Reduced LVDS (TRLVDS DC Specification)

Over Recommended Operating Conditions

Symbol	Description	Min.	Nom.	Max.	Units
V_{CCO}	Driver supply voltage (+/- 5%)	3.14	3.3	3.47	V
V_{ID}	Input differential voltage	150		1200	mV
V_{ICM}	Input common mode voltage	3		3.265	V
V_{CCO}	Termination supply voltage	3.14	3.3	3.47	V
R_T	Termination resistance (off-chip)	45	50	55	Ohms

Note: LatticeECP3 only supports the TRLVDS receiver.



Mini LVDS

Over Recommended Operating Conditions

Parameter Symbol	Description	Min.	Typ.	Max.	Units
Z_O	Single-ended PCB trace impedance	30	50	75	ohms
R_T	Differential termination resistance	50	100	150	ohms
V_{OD}	Output voltage, differential, $\|V_{OP} - V_{OM}\|$	300	—	600	mV
V_{OS}	Output voltage, common mode, $\|V_{OP} + V_{OM}\|/2$	1	1.2	1.4	V
ΔV_{OD}	Change in V_{OD}, between H and L	—	—	50	mV
ΔV_{ID}	Change in V_{OS}, between H and L	—	—	50	mV
V_{THD}	Input voltage, differential, $\|V_{INP} - V_{INM}\|$	200	—	600	mV
V_{CM}	Input voltage, common mode, $\|V_{INP} + V_{INM}\|/2$	$0.3+(V_{THD}/2)$	—	$2.1-(V_{THD}/2)$	
T_R, T_F	Output rise and fall times, 20% to 80%	—	—	550	ps
T_{ODUTY}	Output clock duty cycle	40	—	60	%

Note: Data is for 6mA differential current drive. Other differential driver current options are available.

Pin Information Summary (Cont.)

Pin Information Summary		ECP3-70E			ECP3-70EA		
Pin Type		484 fpBGA	672 fpBGA	1156 fpBGA	484 fpBGA	672 fpBGA	1156 fpBGA
Emulated Differential I/O per Bank	Bank 0	21	30	43	21	30	43
	Bank 1	18	24	39	18	24	39
	Bank 2	10	15	16	8	12	13
	Bank 3	23	27	39	20	23	33
	Bank 6	26	30	39	22	25	33
	Bank 7	14	20	22	11	16	18
	Bank 8	12	12	12	12	12	12
High-Speed Differential I/O per Bank	Bank 0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0
	Bank 2	4	6	6	6	9	9
	Bank 3	6	8	10	9	12	16
	Bank 6	7	9	10	11	14	16
	Bank 7	6	8	9	9	12	13
	Bank 8	0	0	0	0	0	0
Total Single-Ended/ Total Differential I/O per Bank	Bank 0	42/21	60/30	86/43	42/21	60/30	86/43
	Bank 1	36/18	48/24	78/39	36/18	48/24	78/39
	Bank 2	28/14	42/21	44/22	28/14	42/21	44/22
	Bank 3	58/29	71/35	98/49	58/29	71/35	98/49
	Bank 6	67/33	79/38	98/49	67/33	78/39	98/49
	Bank 7	40/20	56/28	62/31	40/20	56/28	62/31
	Bank 8	24/12	24/12	24/12	24/12	24/12	24/12
DDR Groups Bonded per Bank	Bank 0	3	5	7	3	5	7
	Bank 1	3	4	7	3	4	7
	Bank 2	2	3	3	2	3	3
	Bank 3	3	4	5	3	4	5
	Bank 6	4	4	5	4	4	5
	Bank 7	3	4	4	3	4	4
	Configuration Bank 8	0	0	0	0	0	0
SERDES Quads		1	2	3	1	2	3

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (K)
LFE3-70E-6FN484C[1]	1.2V	-6	Lead-Free fpBGA	484	COM	67
LFE3-70E-7FN484C[1]	1.2V	-7	Lead-Free fpBGA	484	COM	67
LFE3-70E-8FN484C[1]	1.2V	-8	Lead-Free fpBGA	484	COM	67
LFE3-70E-6FN672C[1]	1.2V	-6	Lead-Free fpBGA	672	COM	67
LFE3-70E-7FN672C[1]	1.2V	-7	Lead-Free fpBGA	672	COM	67
LFE3-70E-8FN672C[1]	1.2V	-8	Lead-Free fpBGA	672	COM	67
LFE3-70E-6FN1156C[1]	1.2V	-6	Lead-Free fpBGA	1156	COM	67
LFE3-70E-7FN1156C[1]	1.2V	-7	Lead-Free fpBGA	1156	COM	67
LFE3-70E-8FN1156C[1]	1.2V	-8	Lead-Free fpBGA	1156	COM	67

1.This device has associated errata. View www.latticesemi.com/documents/ds1021.zip for a description of the errata.

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (K)
LFE3-95EA-6FN484C	1.2V	-6	Lead-Free fpBGA	484	COM	92
LFE3-95EA-7FN484C	1.2V	-7	Lead-Free fpBGA	484	COM	92
LFE3-95EA-8FN484C	1.2V	-8	Lead-Free fpBGA	484	COM	92
LFE3-95EA-6FN672C	1.2V	-6	Lead-Free fpBGA	672	COM	92
LFE3-95EA-7FN672C	1.2V	-7	Lead-Free fpBGA	672	COM	92
LFE3-95EA-8FN672C	1.2V	-8	Lead-Free fpBGA	672	COM	92
LFE3-95EA-6FN1156C	1.2V	-6	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-7FN1156C	1.2V	-7	Lead-Free fpBGA	1156	COM	92
LFE3-95EA-8FN1156C	1.2V	-8	Lead-Free fpBGA	1156	COM	92

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (K)
LFE3-95E-6FN484C[1]	1.2V	-6	Lead-Free fpBGA	484	COM	92
LFE3-95E-7FN484C[1]	1.2V	-7	Lead-Free fpBGA	484	COM	92
LFE3-95E-8FN484C[1]	1.2V	-8	Lead-Free fpBGA	484	COM	92
LFE3-95E-6FN672C[1]	1.2V	-6	Lead-Free fpBGA	672	COM	92
LFE3-95E-7FN672C[1]	1.2V	-7	Lead-Free fpBGA	672	COM	92
LFE3-95E-8FN672C[1]	1.2V	-8	Lead-Free fpBGA	672	COM	92
LFE3-95E-6FN1156C[1]	1.2V	-6	Lead-Free fpBGA	1156	COM	92
LFE3-95E-7FN1156C[1]	1.2V	-7	Lead-Free fpBGA	1156	COM	92
LFE3-95E-8FN1156C[1]	1.2V	-8	Lead-Free fpBGA	1156	COM	92

1.This device has associated errata. View www.latticesemi.com/documents/ds1021.zip for a description of the errata.

Part Number	Voltage	Grade	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672C	1.2V	-6	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7FN672C	1.2V	-7	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8FN672C	1.2V	-8	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6FN1156C	1.2V	-6	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7FN1156C	1.2V	-7	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8FN1156C	1.2V	-8	Lead-Free fpBGA	1156	COM	149

Date	Version	Section	Change Summary
November 2009 (cont.)	01.5 (cont.)	Architecture (cont.)	Updated Table 2-13, SERDES Standard Support to include SONET/ SDH and updated footnote 2.
		DC and Switching Characterisitcs	Added footnote to ESD Performance table.
			Updated SERDES Power Supply Requirements table and footnotes.
			Updated Maximum I/O Buffer Speed table.
			Updated Pin-to-Pin Peformance table.
			Updated sysCLOCK PLL Timing table.
			Updated DLL timing table.
			Updated High-Speed Data Transmitter tables.
			Updated High-Speed Data Receiver table.
			Updated footnote for Receiver Total Jitter Tolerance Specification table.
			Updated Periodic Receiver Jitter Tolerance Specification table.
			Updated SERDES External Reference Clock Specification table.
			Updated PCI Express Electrical and Timing AC and DC Characteristics.
			Deleted Reference Clock table for PCI Express Electrical and Timing AC and DC Characteristics.
			Updated SMPTE AC/DC Characteristics Transmit table.
			Updated Mini LVDS table.
			Updated RSDS table.
			Added Supply Current (Standby) table for EA devices.
			Updated Internal Switching Characteristics table.
			Updated Register-to-Register Performance table.
			Added HDMI Electrical and Timing Characteristics data.
			Updated Family Timing Adders table.
			Updated sysCONFIG Port Timing Specifications table.
			Updated Recommended Operating Conditions table.
			Updated Hot Socket Specifications table.
			Updated Single-Ended DC table.
			Updated TRLVDS table and figure.
			Updated Serial Data Input Specifications table.
			Updated HDMI Transmit and Receive table.
		Ordering Information	Added LFE3-150EA “TW” devices and footnotes to the Commercial and Industrial tables.
March 2010	01.6	Architecture	Added Read-Before-Write information.
		DC and Switching Characteristics	Added footnote #6 to Maximum I/O Buffer Speed table.
			Corrected minimum operating conditions for input and output differential voltages in the Point-to-Point LVDS table.
		Pinout Information	Added pin information for the LatticeECP3-70EA and LatticeECP3-95EA devices.
		Ordering Information	Added ordering part numbers for the LatticeECP3-70EA and LatticeECP3-95EA devices.
			Removed dual mark information.